

L Number	Hits	Search	DB	Time stamp
1	896	laser n: ((alignment align\$3) adj mark)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/07 11:19
8	2	(laser near15 ((alignment align\$3) adj mark)) same ((alpha or amorphous or a) adj silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/07 11:22
15	21	(laser near15 ((alignment align\$3) adj mark)) and ((alpha or amorphous or a) adj silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/07 11:23
22	47562	TFT (thin adj film adj (transistor device))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/07 11:40
29	4014	(deposit\$3 form\$3 anneal\$3 heat\$3 oxidis\$3 oxidiz\$3) near10 (dielectric insulation oxide dioxide SiO2 "SiO.sub.2" SiO) near10 (protect\$3 prevent\$3) near10 etch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/07 11:47
36	202	(TFT (thin adj film adj (transistor device))) and ((deposit\$3 form\$3 anneal\$3 heat\$3 oxidis\$3 oxidiz\$3) near10 (dielectric insulation oxide dioxide SiO2 "SiO.sub.2" SiO) near10 (protect\$3 prevent\$3) near10 etch\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/07 11:46
43	1763	((deposit\$3 form\$3 anneal\$3 heat\$3 oxidis\$3 oxidiz\$3) near10 (dielectric insulation oxide dioxide SiO2 "SiO.sub.2" SiO) near10 (protect\$3 prevent\$3) near10 etch\$3) near15 (si silicon semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/07 11:48
50	108	(TFT (thin adj film adj (transistor device))) and (((deposit\$3 form\$3 anneal\$3 heat\$3 oxidis\$3 oxidiz\$3) near10 (dielectric insulation oxide dioxide SiO2 "SiO.sub.2" SiO) near10 (protect\$3 prevent\$3) near10 etch\$3) near15 (si silicon semiconductor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/07 11:48